

The filing fee is calculated below on the basis of the claims existing in the prior application as amended at 1 and 2 on the previous page:

	No. Filed	No. Extra	Rate	Fee
TOTAL CLAIMS	38 - 20 =	18	x 18 =	\$324.00
INDEPENDENT CLAIMS	11 - 3 =	8	x 18 =	\$640.00
[] MULTIPLE DEPENDENT CLAIMS PRESENTED				\$0.00
BASIC FEE				\$710.00
TOTAL				\$1,674.00

6. ☐ Small Entity Status:

- a. ☐ A small entity statement is enclosed.
- b. ☐ A small entity statement was filed in the prior nonprovisional application and such status is still proper and desired.
- c. ☐ Is no longer claimed.

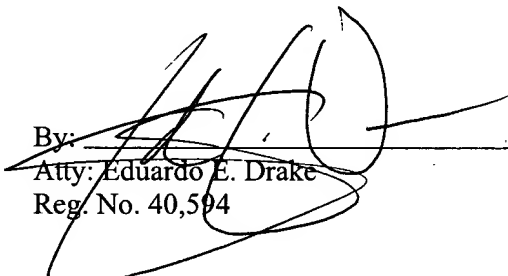
7. ☐ A check in the amount of \$0.00 is attached to pay the filing fee.

8. ☒ The Commissioner is hereby authorized to charge \$1,674.00 to Deposit Account No. 19-0743.

9. ☐ A petition for extension of time in the prior application is enclosed along with a check in the amount of \$0.00 to pay the extension fee.

10. ☐ Other : _____

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This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to Box CPA, Commissioner for Patents, Washington, D. C. 20231.

S/N 09/069,668



PATENT

H15/c
3-7-01
JWR

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al

Examiner: W. David Coleman

Serial No.: 09/069,668

Group Art Unit: 2823

Filed: April 29, 1998

Docket: 303.466US1

Title: BIPOLAR TRANSISTORS WITH LOW-RESISTANCE EMITTER CONTACTS

PRELIMINARY AMENDMENT

Box CPA
Commissioner for Patents
Washington, D.C. 20231

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Before taking up the above-identified application for examination, please enter the following amendments.

IN THE CLAIMS

Please amend the claims as follows:

1. (Amended) A method of making an emitter contact for an emitter region of a bipolar transistor, the method comprising:

C1 forming a polysilicon structure over an emitter region position of a semiconductive substrate, the substrate having a surface at the emitter region position; and [substituting] cross-diffusing metal [for] and at least a portion of the polysilicon structure to produce a metal emitter contact entirely above the surface of the substrate at the emitter region position.

C2 7. (Amended) The method of claim 1 wherein [substituting] cross-diffusing metal [for] and the polysilicon structure comprises [substituting] cross-diffusing metal [for] and substantially all of the polysilicon structure.

8. (Amended) The method of claim 1 wherein [substituting] cross-diffusing metal [for at least a] and the portion of the polysilicon structure, comprises:
depositing metal on the polysilicon structure; and
urging diffusion of the deposited metal into the polysilicon structure.

C3 10. (Amended) The method of claim 1 wherein [substituting] cross-diffusing metal [for at least a] and the portion of the polysilicon structure comprises: